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WeEn Semiconductors



TYN16-600RT



SCR

Rev. 1 — 2 July 2012

Product data sheet

1. Product profile

1.1 General description

Planar passivated Silicon Controlled Rectifier (SCR) in a SOT78 (TO-220AB) plastic package intended for use in applications requiring very high inrush current capability, high thermal cycling performance and high junction temperature capability ($T_{i(max)} = 150$ °C).

1.2 Features and benefits

- High junction operating temperature capability
- High thermal cycling performance
- High voltage capability

- Planar passivated for voltage ruggedness and reliability
- Very high current surge capability

1.3 Applications

- Ignition circuits
- Motor control

- Protection circuits e.g. SMPS inrush current
- Voltage regulation

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	600	V
V_{RRM}	repetitive peak reverse voltage		-	-	600	V
I _{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 10 \text{ ms}$; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	-	210	Α
		half sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 8.3 \text{ms}$	-	-	231	Α
Tj	junction temperature		-	-	150	°C
I _{T(AV)}	average on-state current	half sine wave; T _{mb} ≤ 134 °C; see <u>Figure 3</u>	-	-	10.2	Α
I _{T(RMS)}	RMS on-state current	half sine wave; T _{mb} ≤ 134 °C; see Figure 1; see Figure 2	-	-	16	Α



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	racteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ see Figure 7	-	4.5	25	mA
Dynamic o	haracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 150 °C; $(V_{DM}$ = 67% of V_{DRM}); exponential waveform; gate open circuit	300	-	-	V/µs

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		. 51 //
2	Α	anode	mb	A 🙀 K G
3	G	gate		sym037
mb	A	mounting base; connected to anode	1 2 3	
			TO-220AB (SOT78)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
TYN16-600RT	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
V_{RRM}	repetitive peak reverse voltage		-	600	V
I _{T(AV)}	average on-state current	half sine wave; $T_{mb} \le 134 ^{\circ}\text{C}$; see Figure 3	-	10.2	Α
I _{T(RMS)}	RMS on-state current	half sine wave; $T_{mb} \le 134$ °C; see Figure 1; see Figure 2	-	16	Α
I _{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 10 \text{ ms}$; see Figure 4; see Figure 5	-	210	Α
		half sine wave; $T_{j(init)} = 25$ °C; $t_p = 8.3$ ms	-	231	Α
I ² t	I ² t for fusing	$t_p = 10 \text{ ms}$; sine-wave pulse	-	220.5	A^2s
dI _T /dt	rate of rise of on-state current	$I_T = 40 \text{ A}$; $I_G = 200 \text{ mA}$; $dI_G/dt = 200 \text{ mA}/\mu\text{s}$	-	50	A/μs
I _{GM}	peak gate current		-	5	Α
V_{RGM}	peak reverse gate voltage		-	5	V
P_{GM}	peak gate power		-	20	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	1	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

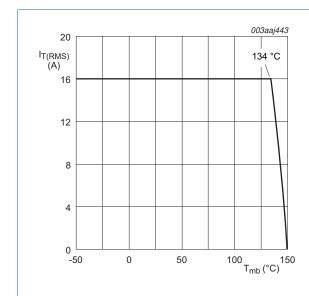


Fig 1. RMS on-state current as a function of mounting base temperature; maximum values

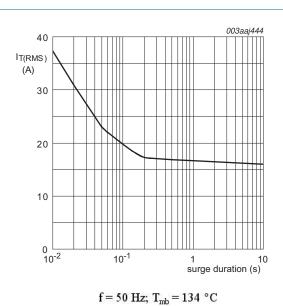


Fig 2. RMS on-state current as a function of surge duration; maximum values

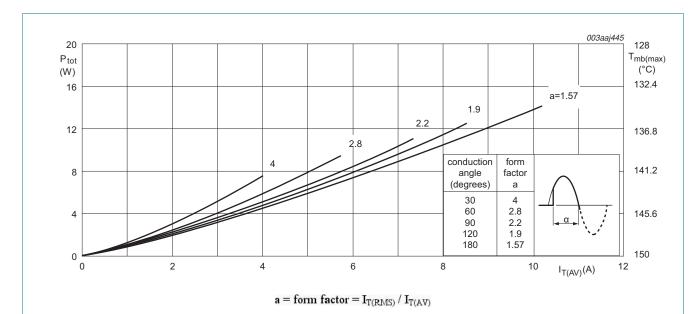


Fig 3. Total power dissipation as a function of average on-state current; maximum values

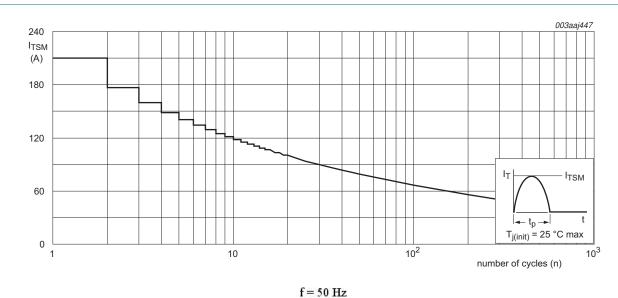
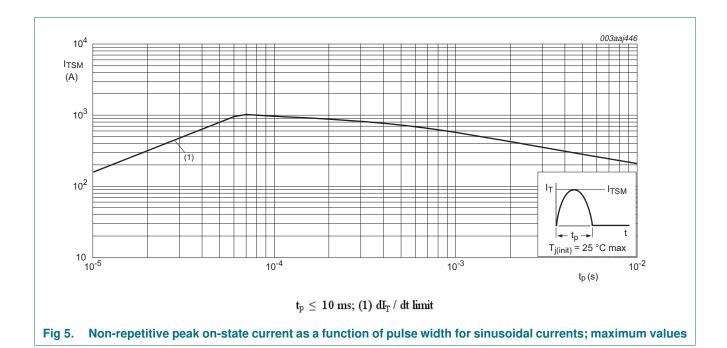


Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



SCR

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 6	-	-	1.1	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W

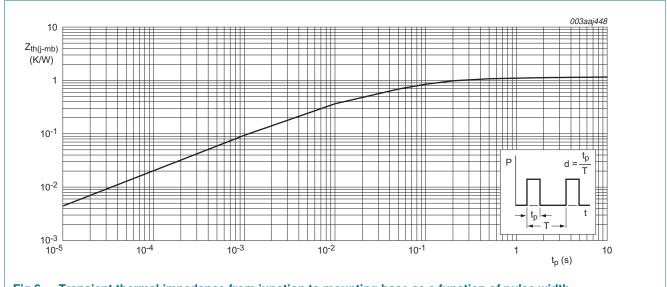


Fig 6. Transient thermal impedance from junction to mounting base as a function of pulse width

6. Characteristics

Table 6. Characteristics

145.00	on an action of the					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T_j = 25 \text{ °C;}$ see Figure 7	-	4.5	25	mA
I _L	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 8</u>	-	21	60	mA
I _H	holding current	$V_D = 12 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 9}}{\text{Minimum of 1}}$	-	16	40	mA
V_{T}	on-state voltage	$I_T = 32 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 10}}{\text{Figure 10}}$	-	1.2	1.5	V
V _{GT}	gate trigger voltage	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T_j = 25 \text{ °C;}$ see Figure 11	-	0.7	1.3	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 150 \text{ °C};$ see Figure 11	0.2	0.4	-	V
I _D	off-state current	V _D = 600 V; T _j = 150 °C	-	0.2	1	mA
I _R	reverse current	$T_j = 150 ^{\circ}\text{C}; V_R = 600 ^{\circ}\text{V}$	-	0.2	1	mA
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	300	-	-	V/µs

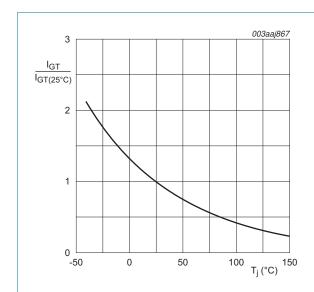


Fig 7. Normalized gate trigger current as a function of junction temperature

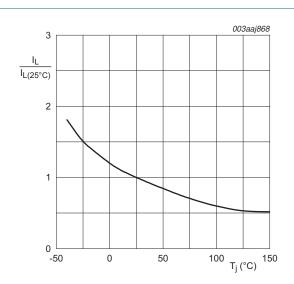
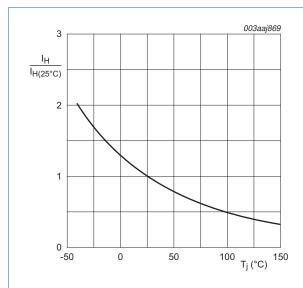
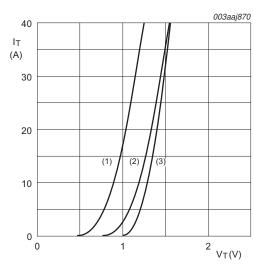


Fig 8. Normalized latching current as a function of junction temperature





 $V_o = 1.0336 \text{ V}; R_s = 0.0141 \Omega$

(1) T_j = 150 °C; typical values

(2) T_j = 150 °C; maximum values

(3) T_i = 25 °C; maximum values

Fig 9. Normalized holding current as a function of junction temperature

Fig 10. On-state current as a function of on-state voltage

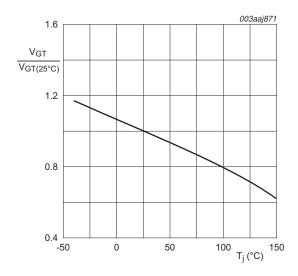
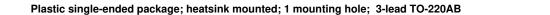
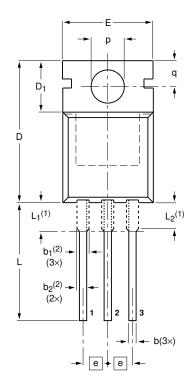


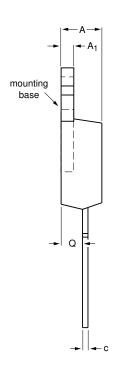
Fig 11. Normalized gate trigger voltage as a function of junction temperature

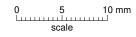
Package outline



SOT78







DIMENSIONS (mm are the original dimensions)

UNI	T A	A ₁	b	b ₁ ⁽²⁾	b ₂ ⁽²⁾	С	D	D ₁	E	е	L	L ₁ (1)	L ₂ ⁽¹⁾ max.	р	q	Q	
mm	1 4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2	

- Lead shoulder designs may vary.
 Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13	

Fig 12. TO-220AB (SOT78)

TYN16-600RT

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
TYN16-600RT v.1	20120702	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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